

## Silicon NPN Power Transistors

## 2SC792

## DESCRIPTION

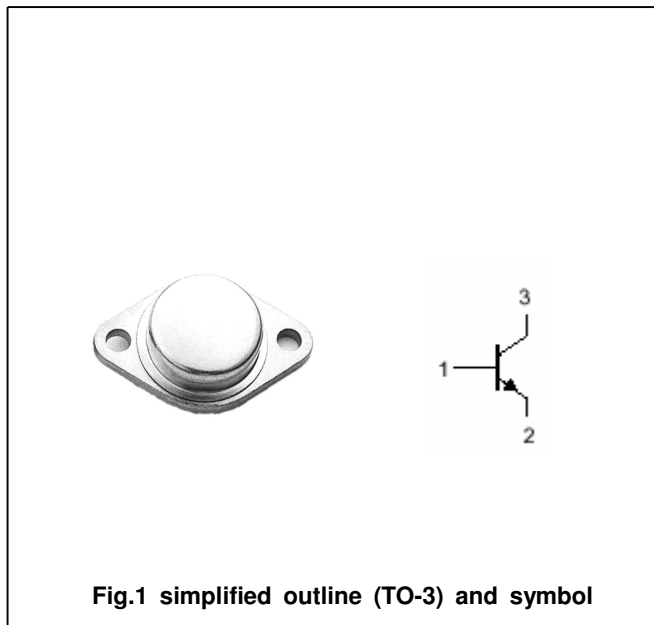
- With TO-3 package
- High breakdown voltage

## APPLICATIONS

- For voltage regulator, inverter, switching mode power supply applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a=?$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	400	V
$V_{CEO}$	Collector-emitter voltage	Open base	300	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		1.5	A
$P_C$	Collector power dissipation	$T_C=25^\circ$	50	W
$T_j$	Junction temperature		150	$^\circ$
$T_{stg}$	Storage temperature		-55~150	$^\circ$

**Silicon NPN Power Transistors****2SC792****CHARACTERISTICS**T<sub>j</sub>=25° unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	300			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1.5A; I <sub>B</sub> =0.3A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =1.5A; I <sub>B</sub> =0.3A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =300V; I <sub>E</sub> =0			50	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			50	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.3A ; V <sub>CE</sub> =10V	30		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =10V		10		MHz

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PACKAGE OUTLINE

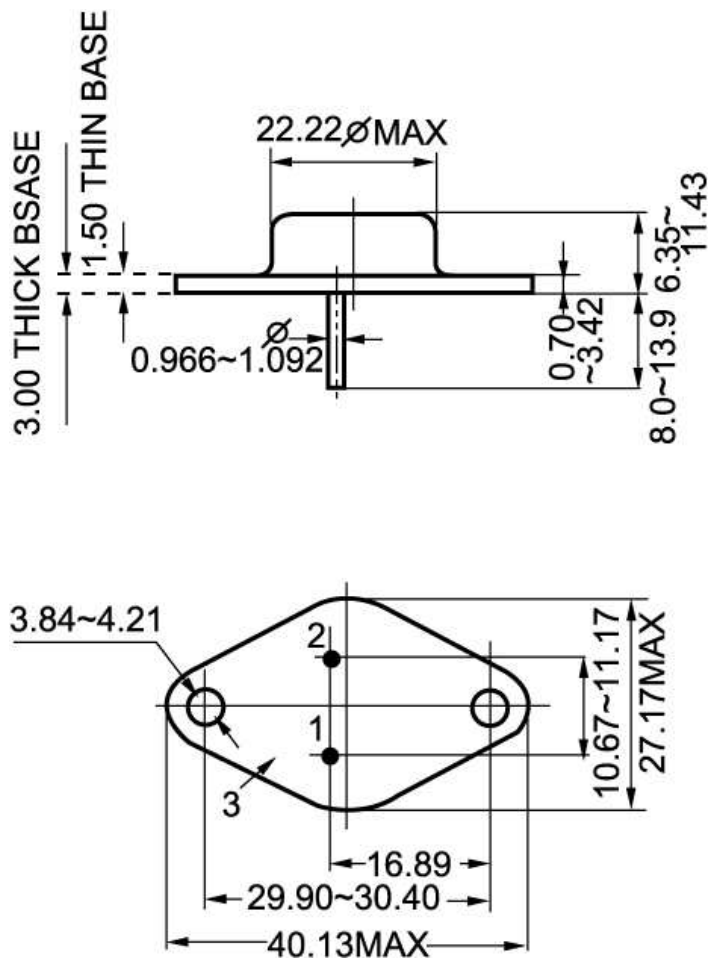


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)

This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.